

FCH041N60E

N-Channel SuperFET® II Easy-Drive MOSFET

600 V, 77 A, 41 mΩ

Features

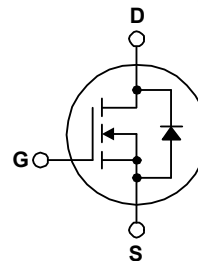
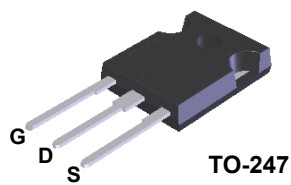
- 650 V @ $T_J = 150^\circ\text{C}$
- Typ. $R_{DS(on)} = 36\text{ m}\Omega$
- Ultra Low Gate Charge (Typ. $Q_g = 285\text{ nC}$)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)} = 735\text{ pF}$)
- 100% Avalanche Tested
- An Integrated Gate Resistor
- RoHS Compliant

Applications

- LCD / LED / PDP TV Lighting
- Solar Inverter
- AC-DC Power Supply

Description

SuperFET® II MOSFET is Fairchild Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET II MOSFET easy-drive series offers slightly slower rise and fall times compared to the SuperFET II MOSFET series. Noted by the "E" part number suffix, this family helps manage EMI issues and allows for easier design implementation. For faster switching in applications where switching losses must be at an absolute minimum, please consider the SuperFET II MOSFET series.



Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FCH041N60E	Unit
V_{DSS}	Drain to Source Voltage	600	V
V_{GSS}	Gate to Source Voltage	- DC	± 20
		- AC ($f > 1\text{ Hz}$)	± 30
I_D	Drain Current	- Continuous ($T_C = 25^\circ\text{C}$)	77
		- Continuous ($T_C = 100^\circ\text{C}$)	48.7
I_{DM}	Drain Current	- Pulsed (Note 1)	231
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	2025
I_{AR}	Avalanche Current	(Note 1)	15
E_{AR}	Repetitive Avalanche Energy	(Note 1)	5.92
dv/dt	MOSFET dv/dt		100
	Peak Diode Recovery dv/dt	(Note 3)	20
P_D	Power Dissipation	($T_C = 25^\circ\text{C}$)	592
		- Derate Above 25°C	4.74
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

Thermal Characteristics

Symbol	Parameter	FCH041N60E	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.21	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	40	

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCH041N60E	FCH041N60E	TO-247	Tube	N/A	N/A	30 units

Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}, T_C = 25^\circ\text{C}$	600	-	-	V
		$I_D = 10\text{ mA}, V_{GS} = 0\text{ V}, T_C = 150^\circ\text{C}$	650	-	-	
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 10\text{ mA}$, Referenced to 25°C	-	0.67	-	$\text{V}/^\circ\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 600\text{ V}, V_{GS} = 0\text{ V}$	-	-	1	μA
		$V_{DS} = 480\text{ V}, V_{GS} = 0\text{ V}, T_C = 125^\circ\text{C}$	-	9.7	-	
I_{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\ \mu\text{A}$	2.5	-	3.5	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}, I_D = 39\text{ A}$	-	36	41	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS} = 20\text{ V}, I_D = 39\text{ A}$	-	71	-	S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 100\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	-	10300	13700	pF
C_{oss}	Output Capacitance		-	355	475	
C_{rss}	Reverse Transfer Capacitance		-	4	6	
C_{oss}	Output Capacitance	$V_{DS} = 380\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	-	187	-	pF
$C_{oss\text{eff}}$	Effective Output Capacitance	$V_{DS} = 0\text{ V to } 480\text{ V}, V_{GS} = 0\text{ V}$	-	735	-	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 380\text{ V}, I_D = 39\text{ A}, V_{GS} = 10\text{ V}$	-	285	380	nC
Q_{gs}	Gate to Source Gate Charge	(Note 4)	-	45	-	
Q_{gd}	Gate to Drain "Miller" Charge		-	105	-	
ESR	Equivalent Series Resistance	$f = 1\text{ MHz}$	-	1.2	-	Ω

Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 380\text{ V}, I_D = 39\text{ A}, V_{GS} = 10\text{ V}, R_G = 4.7\ \Omega$	-	50	110	ns
t_r	Turn-On Rise Time		-	50	110	
$t_{d(off)}$	Turn-Off Delay Time		-	320	650	
t_f	Turn-Off Fall Time	(Note 4)	-	85	180	ns

Drain-Source Diode Characteristics

I_S	Maximum Continuous Drain to Source Diode Forward Current	-	-	77	A	
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current	-	-	231	A	
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_{SD} = 39\text{ A}$	-	-	1.2	V
t_{rr}	Reverse Recovery Time	$V_{GS} = 0\text{ V}, I_{SD} = 39\text{ A}, di_F/dt = 100\text{ A}/\mu\text{s}$	-	590	-	ns
Q_{rr}	Reverse Recovery Charge		-	18	-	

Notes:

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. $I_{AS} = 15\text{ A}, R_G = 25\ \Omega$, starting $T_J = 25^\circ\text{C}$.
3. $I_{SD} \leq 39\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq 380\text{ V}$, starting $T_J = 25^\circ\text{C}$.
4. Essentially independent of operating temperature.

Typical Characteristics

Figure 1. On-Region Characteristics

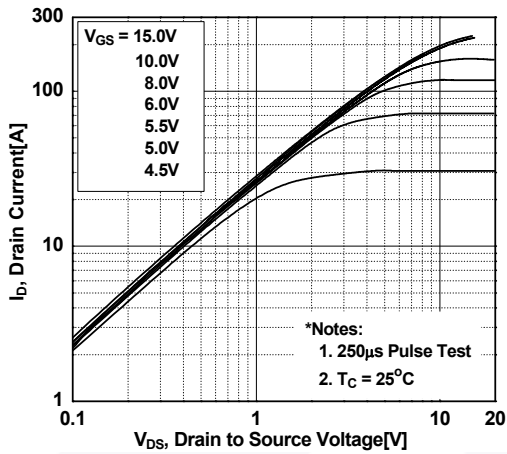


Figure 2. Transfer Characteristics

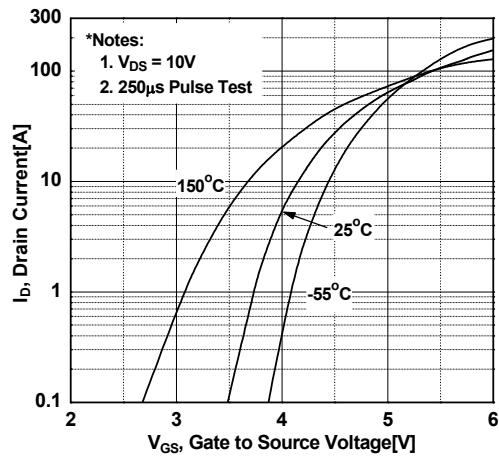


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

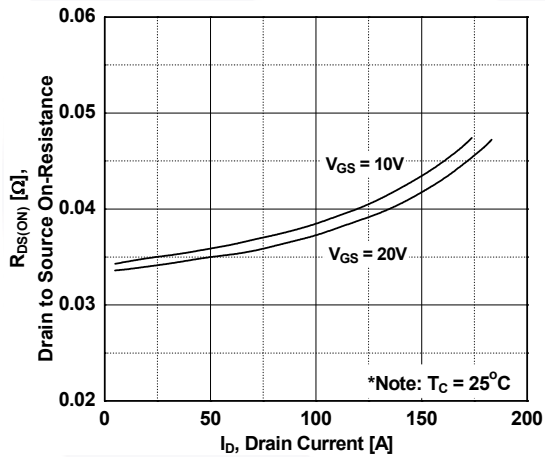


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

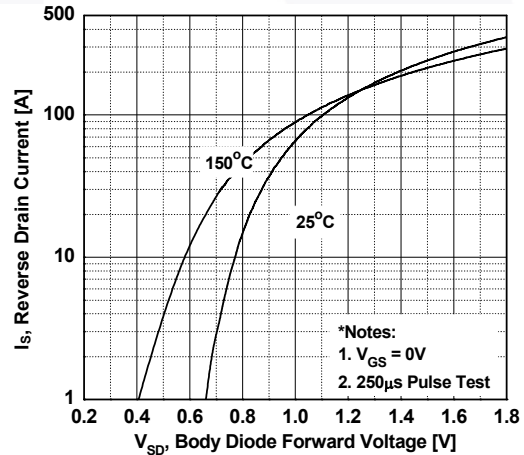


Figure 5. Capacitance Characteristics

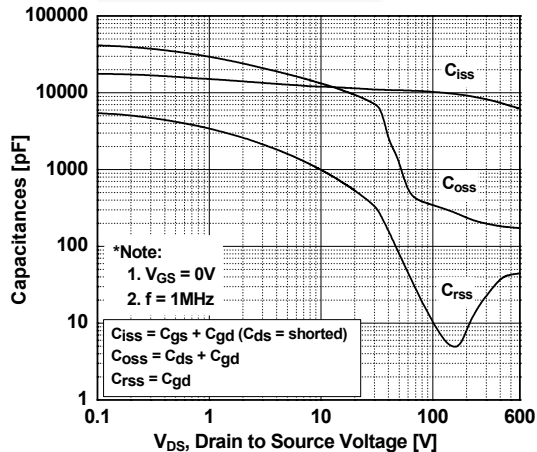
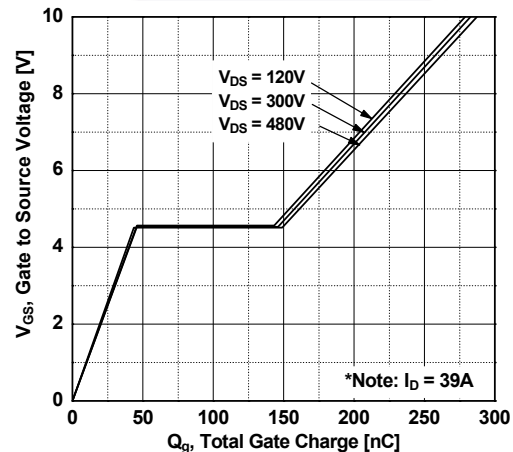


Figure 6. Gate Charge Characteristics



Typical Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

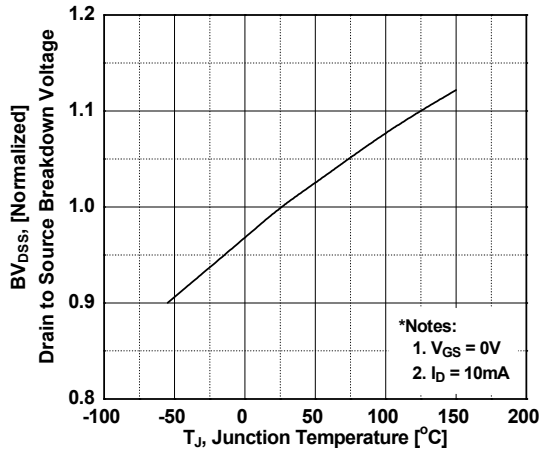


Figure 8. On-Resistance Variation vs. Temperature

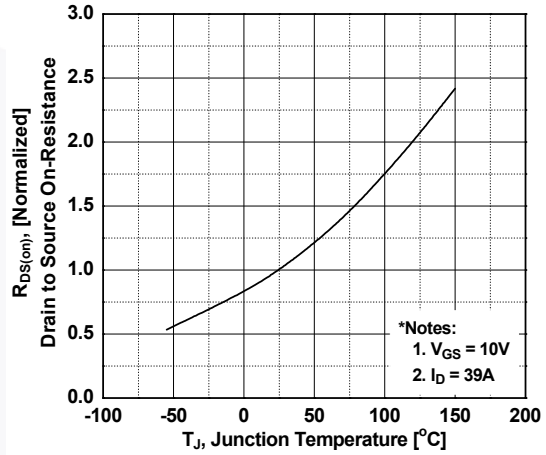


Figure 9. Maximum Safe Operating Area

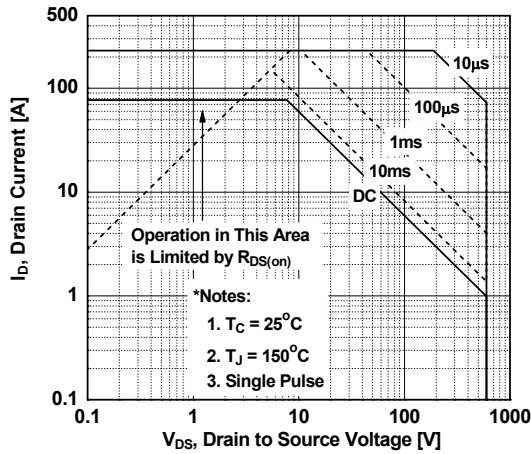


Figure 10. Maximum Drain Current vs. Case Temperature

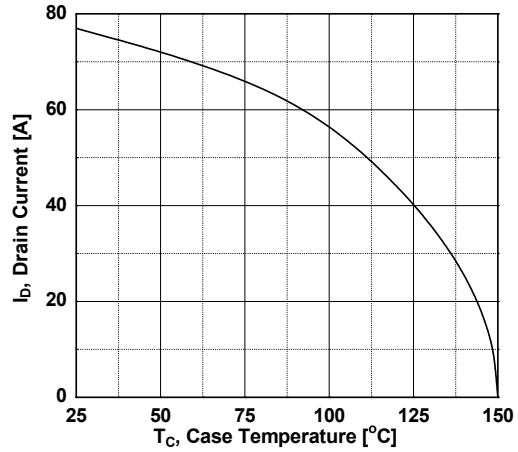
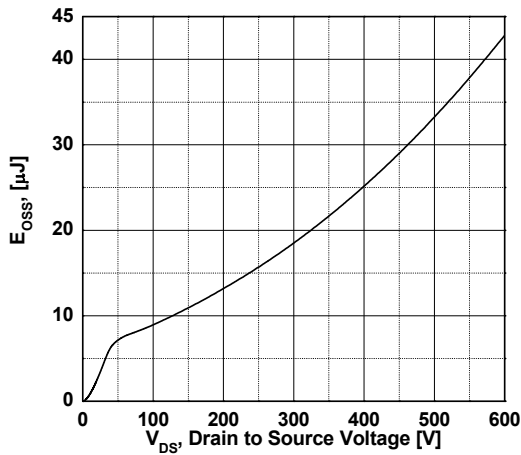
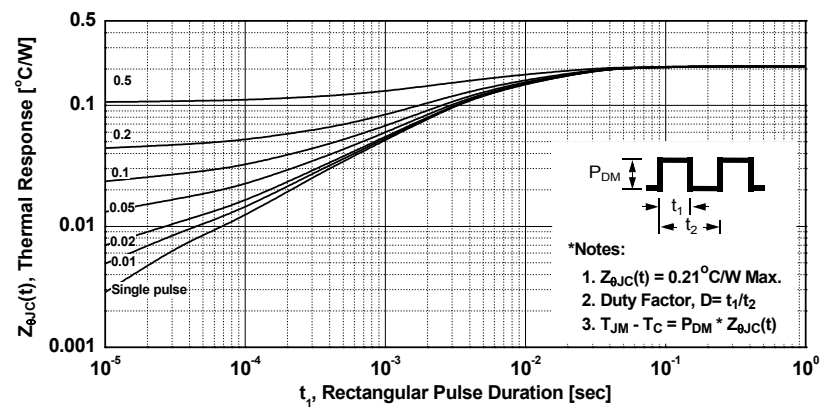


Figure 11. E_oss vs. Drain to Source Voltage



Typical Characteristics (Continued)

Figure 12. Transient Thermal Response Curve



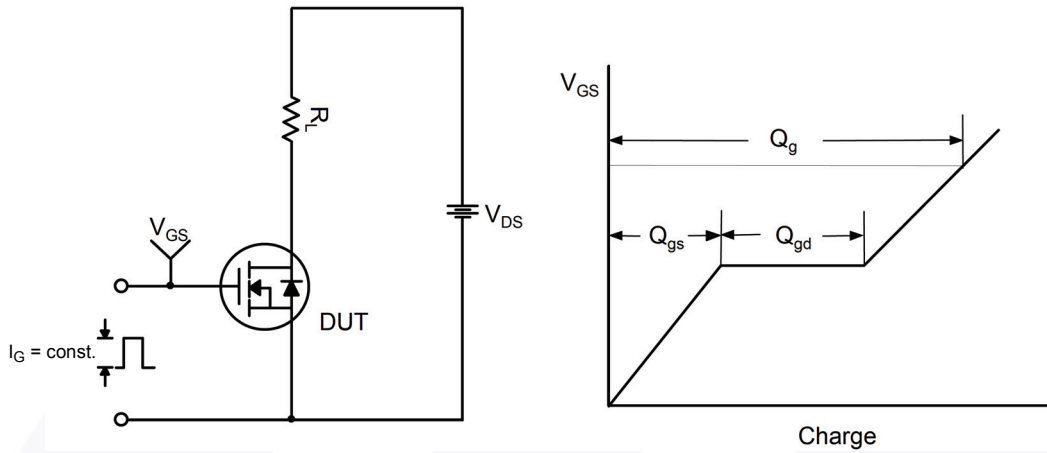


Figure 13. Gate Charge Test Circuit & Waveform



Figure 14. Resistive Switching Test Circuit & Waveforms



Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

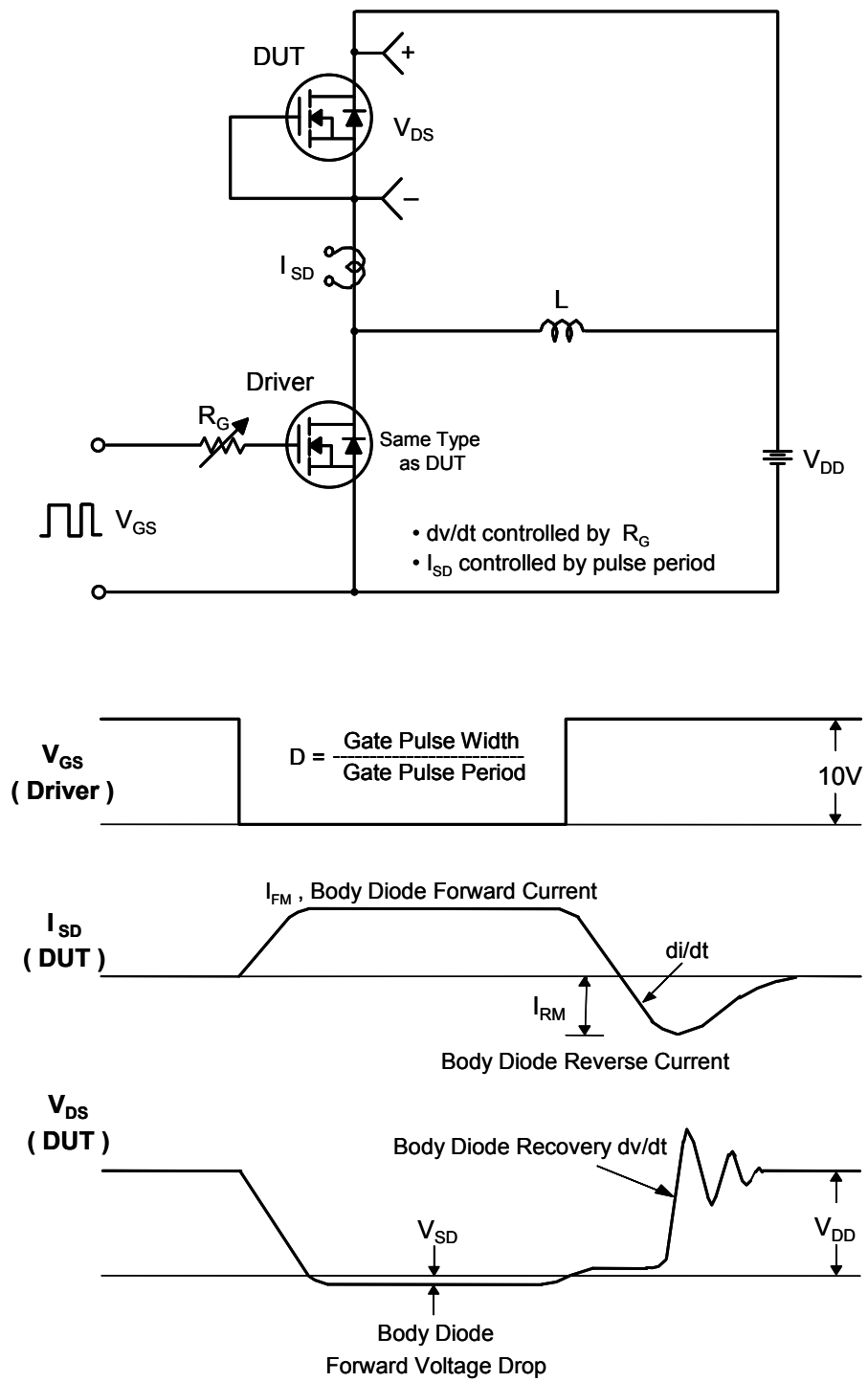
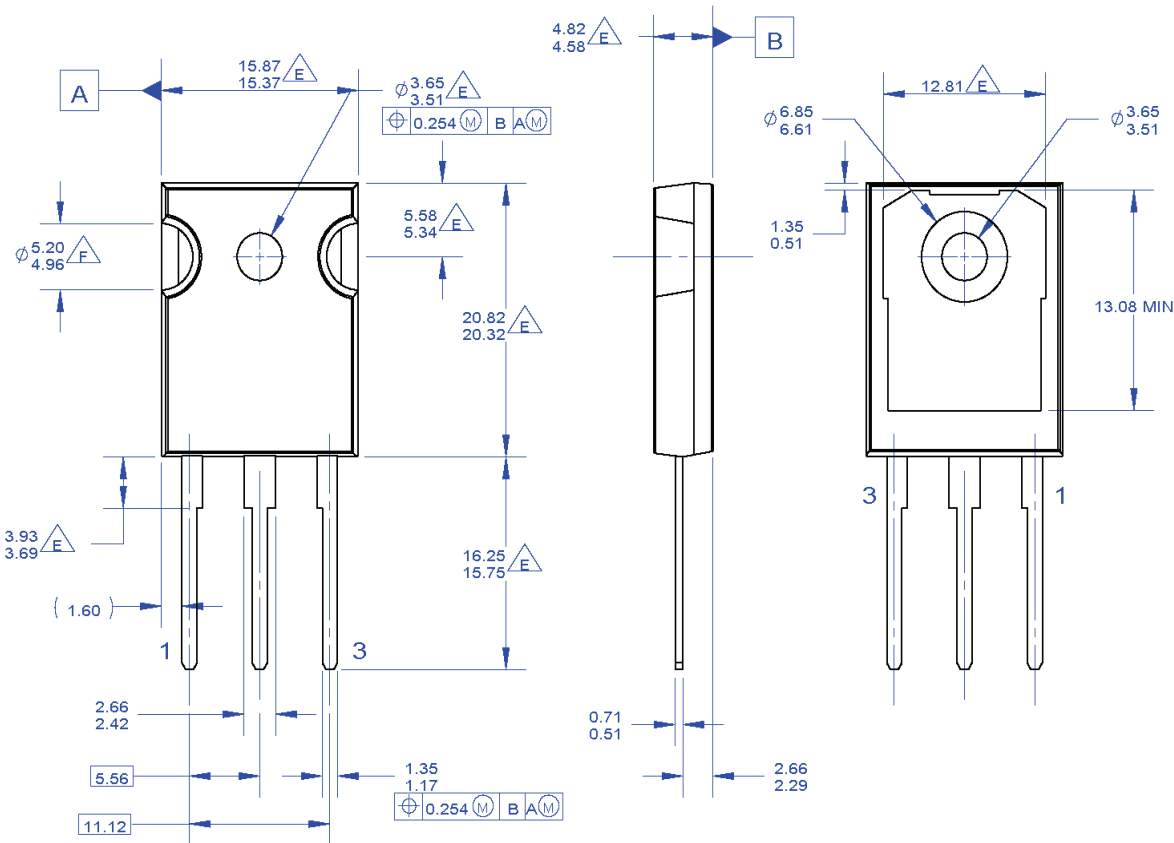


Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions



NOTES: UNLESS OTHERWISE SPECIFIED.

- A. PACKAGE REFERENCE: JEDEC TO-247, ISSUE E, VARIATION AB, DATED JUNE, 2004.
- B. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSIONS.
- C. ALL DIMENSIONS ARE IN MILLIMETERS.
- D. DRAWING CONFORMS TO ASME Y14.5 - 1994

$\triangle E$ DOES NOT COMPLY JEDEC STANDARD VALUE

$\triangle F$ NOTCH MAY BE SQUARE

G. DRAWING FILENAME: MKT-TO247A03_REV03

Figure 17. TO-247, Molded, 3-Lead, Jedec Variation AB

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